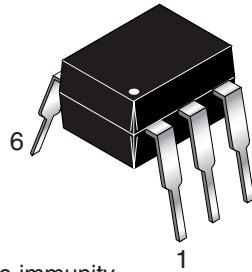


**MOC119**

**DESCRIPTION**

The MOC119 device has a gallium arsenide infrared emitting diode coupled to a silicon darlington phototransistor.

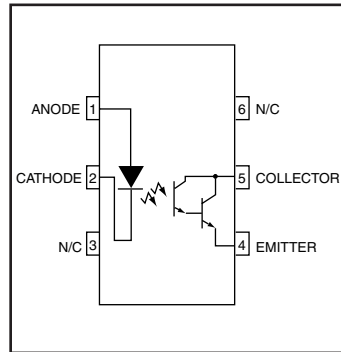


**FEATURES**

- High current transfer ratio of 300%
- No base connection for improved noise immunity
- Underwriters Laboratory (UL) recognized File# E90700

**APPLICATIONS**

- Appliances, measuring instruments
- I/O interface for computers
- Programmable controllers
- Portable electronics
- Interfacing and coupling systems of different potentials and impedance
- Solid state relays



**PACKAGE DIMENSIONS**

**NOTE**  
All dimensions are in inches (millimeters)

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^\circ\text{C}$ Unless otherwise specified.)			
Parameter	Symbol	Value	Units
<b>TOTAL DEVICE</b>			
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operating Temperature	$T_{OPR}$	-55 to +100	$^\circ\text{C}$
Lead Solder Temperature	$T_{SOL}$	260 for 10 sec	$^\circ\text{C}$
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	250	mW
Derate above $25^\circ\text{C}$		2.94	mW/ $^\circ\text{C}$
Input-Output Isolation Voltage	$V_{ISO}$	5300	Vac(rms)
<b>EMITTER</b>			
DC/Average Forward Input Current	$I_F$	60	mA
Reverse Input Voltage	$V_R$	3	V
LED Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	120	mW
Derate above $25^\circ\text{C}$		1.41	mW/ $^\circ\text{C}$
<b>DETECTOR</b>			
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector Voltage	$V_{ECO}$	7	V
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Derate above $25^\circ\text{C}$		1.76	mW/ $^\circ\text{C}$
Continuous Collector Current	$I_C$	150	mA

**MOC119**
**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  Unless otherwise specified.)

**INDIVIDUAL COMPONENT CHARACTERISTICS**

Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
<b>EMITTER</b>						
Input Forward Voltage	( $I_F = 10\text{ mA}$ )	$V_F$		1.15	1.5	V
Input Capacitance	( $V_R = 0, f = 1\text{ MHz}$ )	$C_{IN}$		18		pF
Reverse Leakage Current	( $V_R = 3.0\text{ V}$ )	$I_R$		0.05	100	$\mu\text{A}$
<b>DETECTOR</b>						
Collector-Emitter Breakdown Voltage	( $I_C = 100\ \mu\text{A}$ )	$BV_{CEO}$	30			V
Emitter-Collector Breakdown Voltage	( $I_E = 10\ \mu\text{A}$ )	$BV_{ECO}$	7			V
Collector-Emitter Dark Current	( $V_{CE} = 10\text{ V}$ )	$I_{CEO}$			100	nA

**TRANSFER CHARACTERISTICS**

DC Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Current Transfer Ratio,	( $I_F = 10\text{ mA}, V_{CE} = 2\text{ V}$ )	CTR	30 (300)	45 (450)		mA (%)

**TRANSFER CHARACTERISTICS**

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
<b>SWITCHING TIMES</b>						
Turn-on Time	( $V_{CE} = 10\text{ V}, R_L = 100\ \Omega, I_F = 5\text{ mA}$ )	$t_{on}$		3.5		$\mu\text{s}$
Turn-off Time		$t_{off}$		95		$\mu\text{s}$

**ISOLATION CHARACTERISTICS**

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Input-Output Isolation Voltage	( $I_{I-O} \leq 1\ \mu\text{A}, 1\text{ min.}$ )	$V_{ISO}$	7500			Vac(pk)
	( $I_{I-O} \leq 1\ \mu\text{A}, 1\text{ min.}$ )		5300			Vac(rms)
Isolation Resistance	( $V_{I-O} = 500\text{ VDC}$ )	$R_{ISO}$		$10^{11}$		$\Omega$
Isolation Capacitance	( $V = 0\text{ V}, f = 1\text{ MHz}$ )	$C_{ISO}$		0.2		pf
Collector - Emitter Saturation Voltage	( $I_C = 10\text{ mA}, I_F = 10\text{ mA}$ )	$V_{CE(SAT)}$			1	V

Note

 \*\* Typical values at  $T_A = 25^\circ\text{C}$

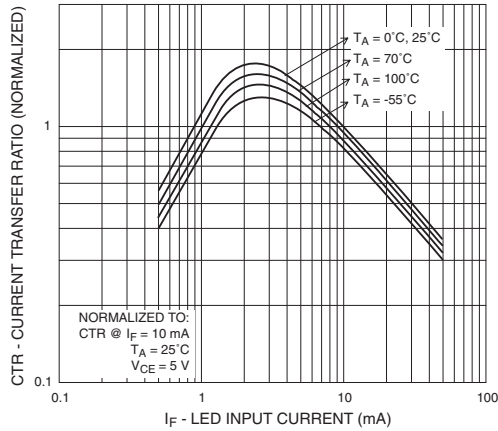


Fig. 1 Output Current vs. Input Current

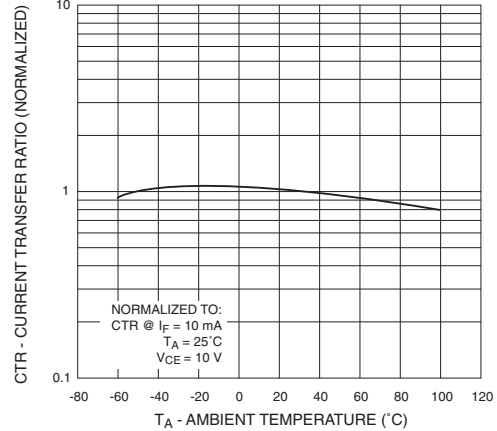


Fig. 2 Current Transfer Ratio vs. Ambient Temperature

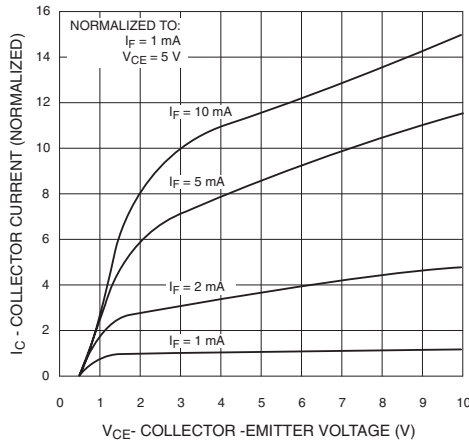


Fig. 3 Collector Current vs. Collector-Emitter Voltage

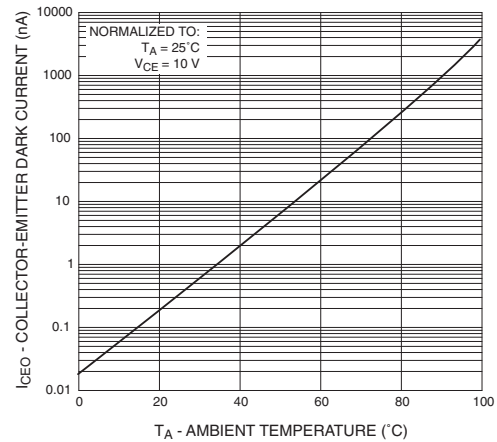


Fig. 4 Dark Current vs. Ambient Temperature

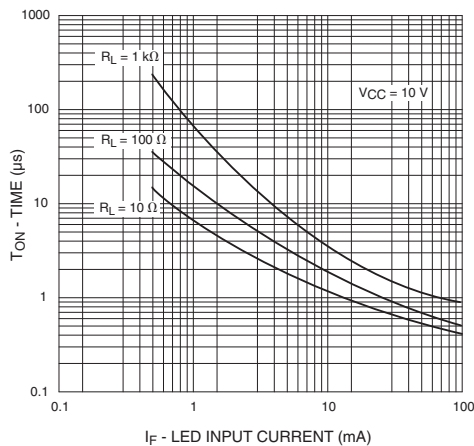


Fig. 5 Turn-On Time vs. Input Current

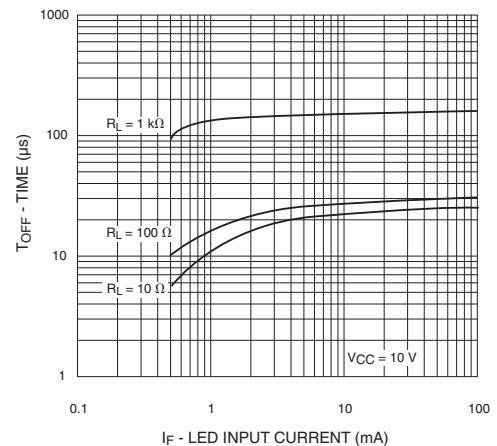
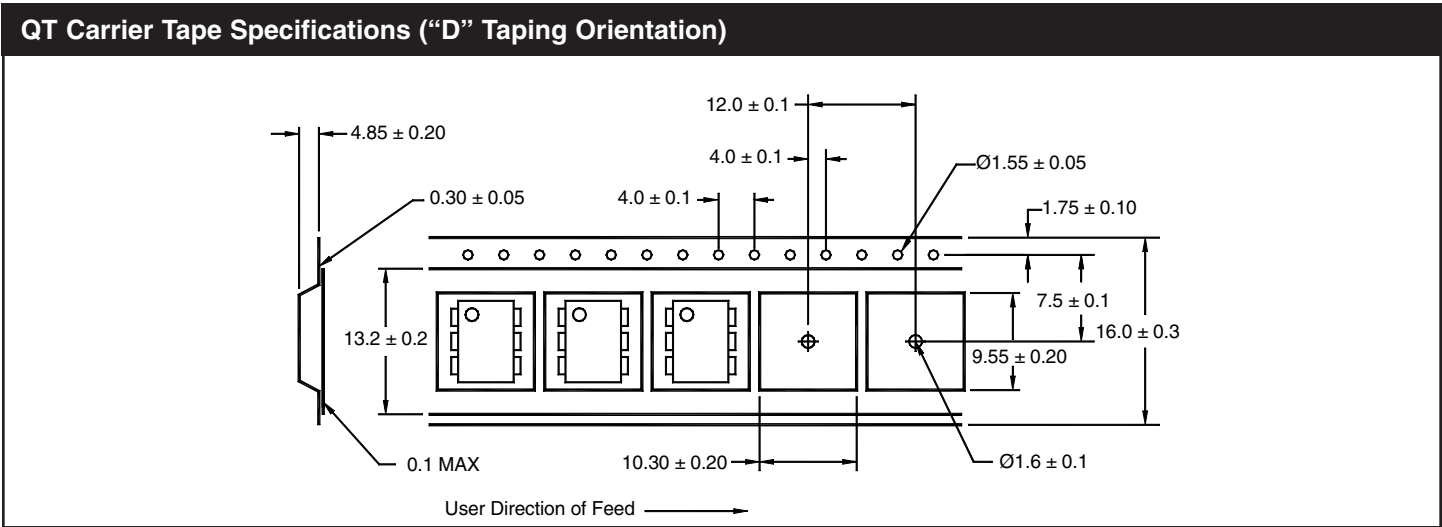


Fig. 6 Turn-Off Time vs. Input Current

**MOC119**

**ORDERING INFORMATION**

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel



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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.